



LY61L2568

Rev. 0.4

256K X 8 BIT HIGH SPEED CMOS SRAM

REVISION HISTORY

<u>Revision</u>	<u>Description</u>	<u>Issue Date</u>
Rev. 0.1	Preliminary	Apr.19.2006
Rev. 0.2	Deleted I _{SB} Spec.	May.24.2006
Rev. 0.3	Deleted -10/-12/-15 Spec.	Mar.13.2007
Rev. 0.4	Revised Test Condition of I _{CC} /I _{SB1} /I _{DR} Revised V _{TERM} to V _{T1} and V _{T2} Revised <u>FEATURES & ORDERING INFORMATION</u> <u>Lead free and green package available</u> to <u>Green package available</u> Deleted T _{SOLDER} in <u>ABSOLUTE MAXIMUM RATINGS</u> Added packing type in <u>ORDERING INFORMATION</u>	Apr.17.2009

FEATURES

- Fast access time : 20/25ns
- **Very low power consumption:**
Operating current(Normal version):
110/90mA(TYP.)
Operating current(20/25ns LL version):
40/35mA(TYP.)
- Standby current(Normal version):
0.5mA(TYP.)
Standby current(20/25ns LL version):
10μA(TYP.)
- Single 3.3V power supply
- All inputs and outputs TTL compatible
- Fully static operation
- Tri-state output
- Data retention voltage : 2.0V (MIN.)
- **Green package available**
- Package : 44-pin 400 mil TSOP-II

GENERAL DESCRIPTION

The LY61L2568 is a 2,097,152-bit low power CMOS static random access memory organized as 262,144 words by 8 bits. It is fabricated using very high performance, high reliability CMOS technology. Its standby current is stable within the range of operating temperature.

The LY61L2568 is well designed for very low power system applications, and particularly well suited for battery back-up nonvolatile memory application.

The LY61L2568 operates from a single power supply of 3.3V and all inputs and outputs are fully TTL compatible

PRODUCT FAMILY

Product Family	Operating Temperature	Vcc Range	Speed	Power Dissipation	
				Standby(IsB1,TYP.)	Operating(Icc,TYP.)
LY61L2568	0 ~ 70°C	3.0 ~ 3.6V	20/25ns	0.5mA	110/90mA
LY61L2568(LL)	0 ~ 70°C	3.0 ~ 3.6V	20/25ns	10μA(LL)	40/35mA(LL)

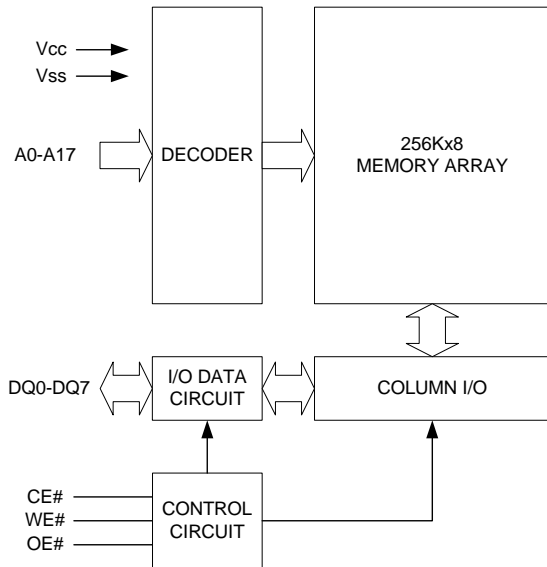


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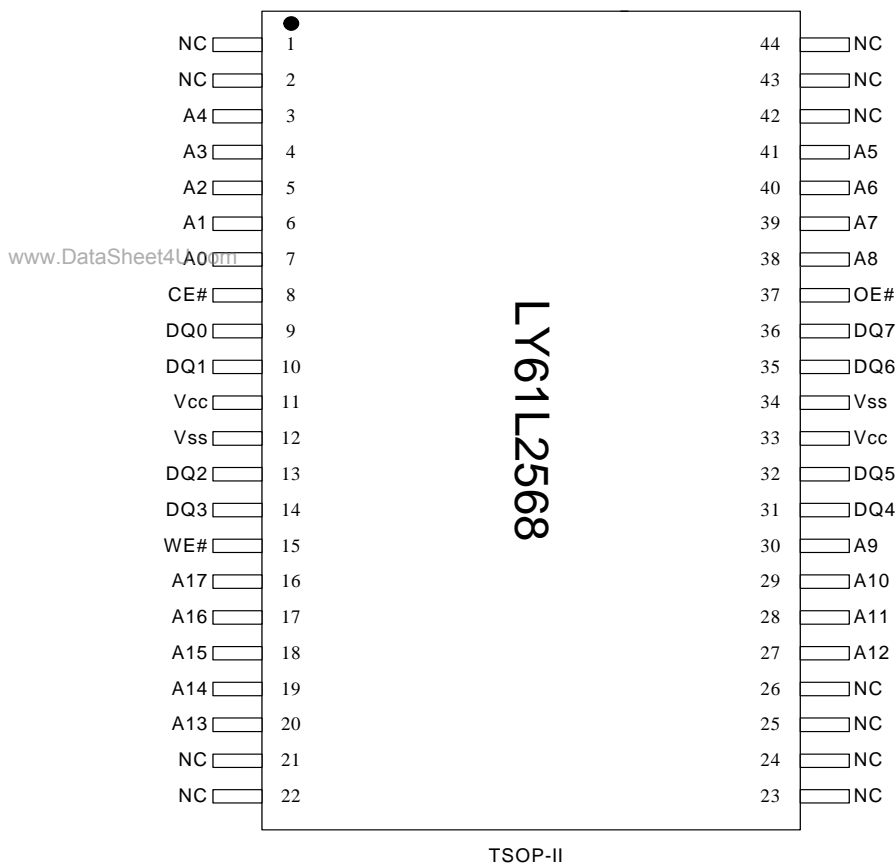
FUNCTIONAL BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A17	Address Inputs
DQ0 – DQ7	Data Inputs/Outputs
CE#	Chip Enable Inputs
WE#	Write Enable Input
OE#	Output Enable Input
Vcc	Power Supply
Vss	Ground
NC	No Connection

PIN CONFIGURATION





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ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Voltage on Vcc relative to Vss	V _{T1}	-0.5 to 4.6	V
Voltage on any other pin relative to Vss	V _{T2}	-0.5 to V _{cc} +0.5	V
Operating Temperature	T _A	0 to 70(C grade)	°C
Storage Temperature	T _{STG}	-65 to 150	°C
Power Dissipation	P _D	1	W
DC Output Current	I _{OUT}	50	mA

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE#	OE#	WE#	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	High-Z	I _{SB1}
Output Disable	L	H	H	High-Z	I _{cc}
Read	L	L	H	D _{OUT}	I _{cc}
Write	L	X	L	D _{IN}	I _{cc}

Note: H = V_{IH}, L = V_{IL}, X = Don't care.

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP. ⁴	MAX.	UNIT	
Supply Voltage	V _{cc}		3.0	3.3	3.6	V	
Input High Voltage	V _{IH} ¹		2.2	-	V _{cc} +0.3	V	
Input Low Voltage	V _{IL} ²		-0.3	-	0.6	V	
Input Leakage Current	I _{LI}	V _{cc} ≥ V _{IN} ≥ V _{ss}	-1	-	1	μA	
Output Leakage Current	I _{LO}	V _{cc} ≥ V _{OUT} ≥ V _{ss} , Output Disabled	-1	-	1	μA	
Output High Voltage	V _{OH}	I _{OH} = -1mA	2.4	-	-	V	
Output Low Voltage	V _{OL}	I _{OL} = 2mA	-	-	0.4	V	
Average Operating Power supply Current	I _{cc}	Cycle time = Min. CE# = V _{IL} , I _{I/O} = 0mA Others at V _{IL} or V _{IH}	20	-	110	150	mA
			25	-	90	115	mA
			20LL	-	40	50	mA
			25LL	-	35	45	mA
Standby Power Supply Current	I _{SB1}	CE# ≥ V _{cc} - 0.2V Others at 0.2V or V _{cc} - 0.2V	Normal	-	0.5	5 ⁵	mA
			20/25LL	-	10	50 ⁶	μA

Notes:

- V_{IH}(max) = V_{cc} + 3.0V for pulse width less than 10ns.
- V_{IL}(min) = V_{ss} - 3.0V for pulse width less than 10ns.
- Over/Undershoot specifications are characterized, not 100% tested.
- Typical values are included for reference only and are not guaranteed or tested.
Typical values are measured at V_{cc} = V_{cc}(TYP.) and T_A = 25°C
- 1mA for special request
- 20μA for special request



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CAPACITANCE (TA = 25°C, f = 1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C _{IN}	-	8	pF
Input/Output Capacitance	C _{I/O}	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0.2V to V _{CC} - 0.2V
Input Rise and Fall Times	3ns
Input and Output Timing Reference Levels	1.5V
Output Load	C _L = 30pF + 1TTL, I _{OH} /I _{OL} = -8mA/16mA

AC ELECTRICAL CHARACTERISTICS

(1) READ CYCLE

PARAMETER	SYM.	LY61L2568-20		LY61L2568-25		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t _{RC}	20	-	25	-	ns
Address Access Time	t _{AA}	-	20	-	25	ns
Chip Enable Access Time	t _{ACE}	-	20	-	25	ns
Output Enable Access Time	t _{OE}	-	8	-	9	ns
Chip Enable to Output in Low-Z	t _{CLZ} *	4	-	4	-	N`s
Output Enable to Output in Low-Z	t _{OLZ} *	0	-	0	-	ns
Chip Disable to Output in High-Z	t _{CHZ} *	-	8	-	9	ns
Output Disable to Output in High-Z	t _{OHZ} *	-	8	-	9	ns
Output Hold from Address Change	t _{OH}	3	-	3	-	ns

(2) WRITE CYCLE

PARAMETER	SYM.	LY61L2568-20		LY61L2568-25		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t _{WC}	20	-	25	-	ns
Address Valid to End of Write	t _{AW}	16	-	20	-	ns
Chip Enable to End of Write	t _{CW}	16	-	20	-	ns
Address Set-up Time	t _{AS}	0	-	0	-	ns
Write Pulse Width	t _{WP}	11	-	12	-	ns
Write Recovery Time	t _{WR}	0	-	0	-	ns
Data to Write Time Overlap	t _{DW}	9	-	10	-	ns
Data Hold from End of Write Time	t _{DH}	0	-	0	-	ns
Output Active from End of Write	t _{OW} *	5	-	6	-	ns
Write to Output in High-Z	t _{WHZ} *	-	9	-	10	ns

*These parameters are guaranteed by device characterization, but not production tested.

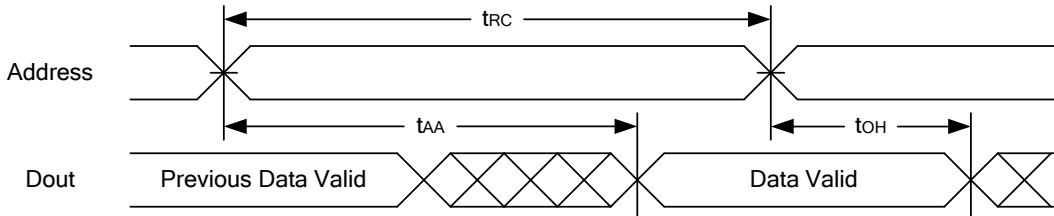
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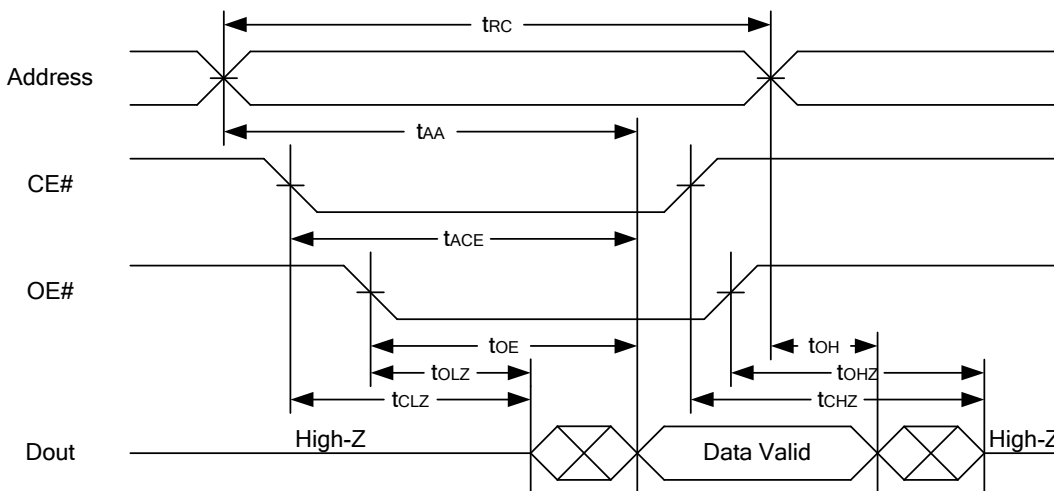
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TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2)



READ CYCLE 2 (CE# and OE# Controlled) (1,3,4,5)



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Notes :

1. WE# is high for read cycle.
2. Device is continuously selected OE# = low, CE# = low.
3. Address must be valid prior to or coincident with CE# = low; otherwise tAA is the limiting parameter.
4. tCLZ, tOLZ, tCHZ and tOHZ are specified with CL = 5pF. Transition is measured ±500mV from steady state.
5. At any given temperature and voltage condition, tCHZ is less than tCLZ, tOHZ is less than tOLZ.



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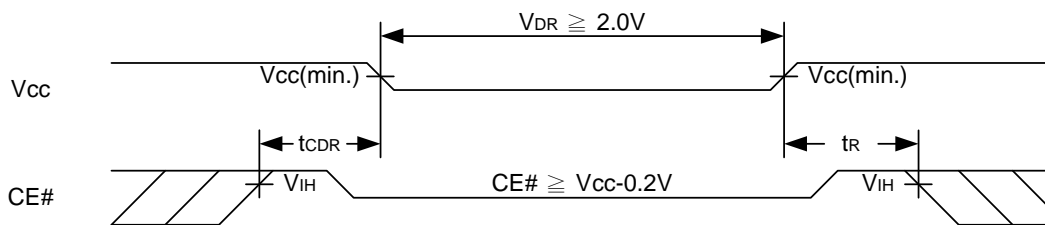
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DATA RETENTION CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Vcc for Data Retention	V _{DR}	CE# ≥ V _{CC} - 0.2V	2.0	-	3.6	V	
Data Retention Current	I _{DR}	V _{CC} = 2.0V CE# ≥ V _{CC} - 0.2V	Normal	-	0.5	1	mA
		Others at 0.2V or V _{CC} - 0.2V	20/25LL	-	5	40	μA
Chip Disable to Data Retention Time	t _{CDR}	See Data Retention Waveforms (below)	0	-	-	ns	
Recovery Time	t _R		t _{RC*}	-	-	ns	

t_{RC*} = Read Cycle Time

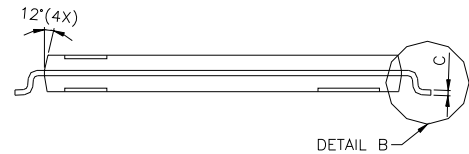
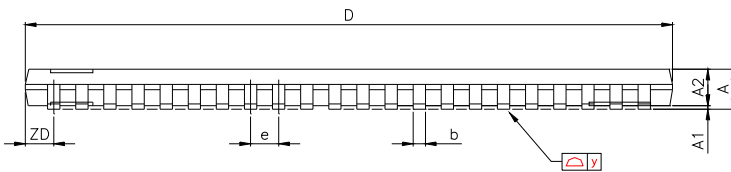
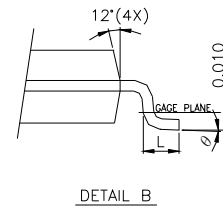
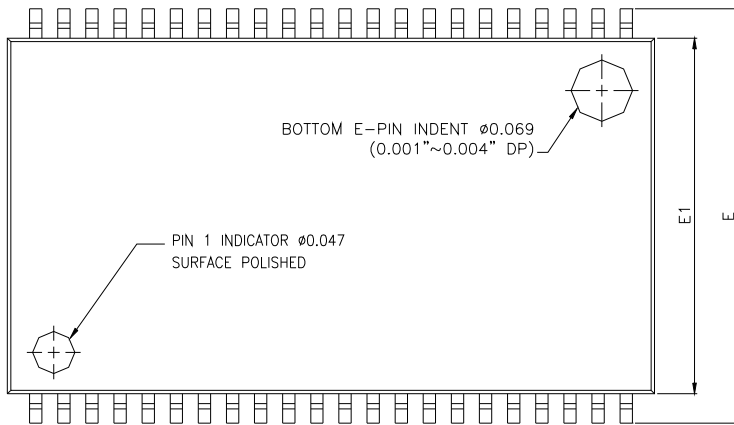
DATA RETENTION WAVEFORM





PACKAGE OUTLINE DIMENSION

44-pin 400mil TSOP-II Package Outline Dimension



SYMBOLS	DIMENSIONS IN MILLMETERS			DIMENSIONS IN MILS		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	-	-	1.20	-	-	47.2
A1	0.05	0.10	0.15	2.0	3.9	5.9
A2	0.95	1.00	1.05	37.4	39.4	41.3
b	0.30	-	0.45	11.8	-	17.7
c	0.12	-	0.21	4.7	-	8.3
D	18.212	18.415	18.618	717	725	733
E	11.506	11.760	12.014	453	463	473
E1	9.957	10.160	10.363	392	400	408
e	-	0.800	-	-	31.5	-
L	0.40	0.50	0.60	15.7	19.7	23.6
ZD	-	0.805	-	-	31.7	-
y	-	-	0.076	-	-	3
θ	0°	3°	6°	0°	3°	6°

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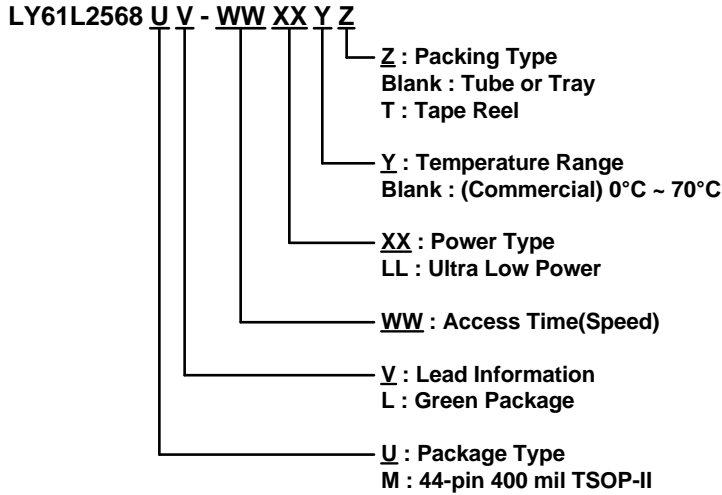


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